Electronic Pate	ent Application F	ee Transm	nittal				
Application Number:	10516358	10516358					
Filing Date:	24-Nov-2004	24-Nov-2004					
Title of Invention:	Method for epitaxis substrate	Method for epitaxial growth of a gallium nitride film separated from its substrate					
First Named Inventor/Applicant Name:	Hacene Lahreche	Hacene Lahreche					
Filer:	Stacie Jo Sundqui:	Stacie Jo Sundquist/Si Vuong					
Attorney Docket Number:	15675P556	15675P556					
Filed as Small Entity	•						
U.S. National Stage under 35 USC 37	1 Filing Fees						
Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)			
Basic Filing:		'					
Pages:							
Claims:	0 0 _ 7						
Claims in excess of 20	2615	71	25	1775			
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							
Extension-of-Time:							

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension - 1 month with \$0 paid	2251	1	60	60
Miscellaneous:				
	Tota	1835		